

SAED 90
Device Parameters

Device nmos12

tox	2.05	nm
Vth0	397	mV
Idsat (Lmin)	869	uA/um
unCox (long)	428	uA/V^2
Xj	15	nm
Gamma	0.4	V^0.5
Cov	26.5	nF/m
CJ	500	uF/m2
CJSW	50	nF/m

Device pmos12

tox	2.15	nm
Vth0	-276	mV
Idsat (Lmin)	-426	uA/um
upCox (long)	-124	uA/V^2
Xj	28	nm
Gamma	0.4	V^0.5
Cov	26.5	nF/m
CJ	500	uF/m2
CJSW	50	nF/m